

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced trench gate super junction technology

650V Super Junction Power MOSFET

Product Summary



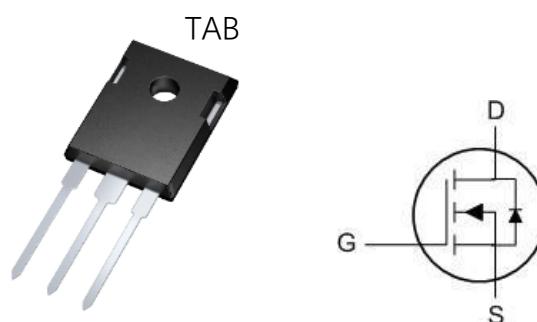
BVDSS	RDS(ON)	ID
650V	36mΩ	85A

Description

The XR65R36H use super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

The XR65R36H meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO-247 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ^{1,6}	300	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ^{1,6}	200	A
I_{DM}	Pulsed Drain Current ²	690	A
EAS	Single Pulse Avalanche Energy ³	500	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	220	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	35	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$\Delta BV_{DSS} / \Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=1A$	---	1.25	1.55	$m\Omega$
		$V_{GS}=4.5V$, $I_D=1A$	---	1.65	2.05	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	1.55	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=40V$, $V_{GS}=0V$, $T_J=150^\circ\text{C}$	---	100	---	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=20V$, $I_D=35A$	---	66	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	2.7	---	Ω
Q_g	Total Gate Charge	$V_{DS}=32V$, $V_{GS}=10V$, $I_D=20A$	---	127	---	nC
Q_{gs}	Gate-Source Charge		---	35	---	
Q_{gd}	Gate-Drain Charge		---	26	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=10V$, $V_{DS}=20V$, $R_G=2\Omega$, $I_D=25A$	---	22.5	---	ns
T_r	Rise Time		---	6.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	80.3	---	
T_f	Fall Time		---	26.9	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1MHz$	---	8300	---	pF
C_{oss}	Output Capacitance		---	1510	---	
C_{rss}	Reverse Transfer Capacitance		---	130	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	300	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=25A$, $T_J=25^\circ\text{C}$	0.7	0.9	1.1	V
t_{rr}	Reverse Recovery Time	$I_F=25A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	100	---	nS
Q_{rr}	Reverse Recovery Charge		---	163	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$ 3.The EAS data shows Max. rating . The test condition is $T_J=25^\circ\text{C}$, $V_{DD}=32V$, $V_{GS}=10V$, $L=0.5mH$ 4.The power dissipation is limited by 150°C junction temperature5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Fig 1. Output Characteristics ($T_j=25^\circ\text{C}$)

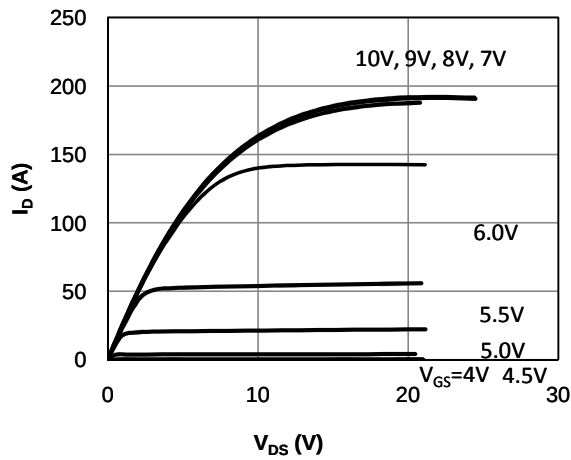


Fig 2. Output Characteristics ($T_j=150^\circ\text{C}$)

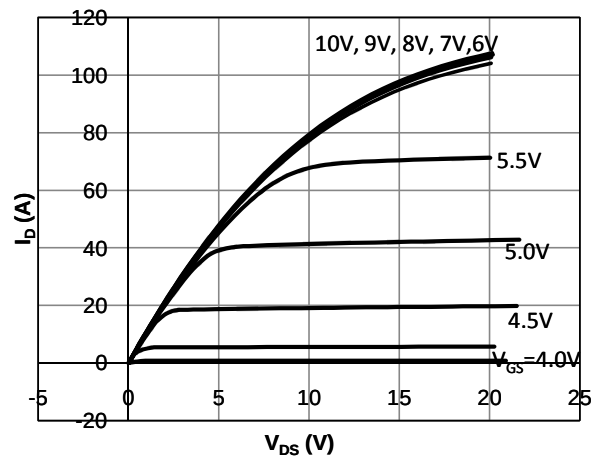


Fig 3: Transfer Characteristics

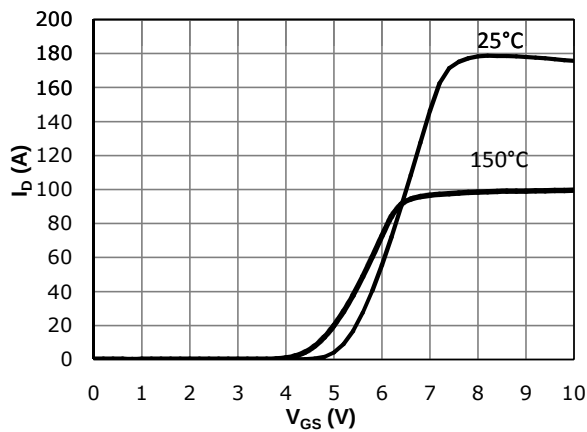


Fig 4: V_{TH} Vs T_j Temperature Characteristics

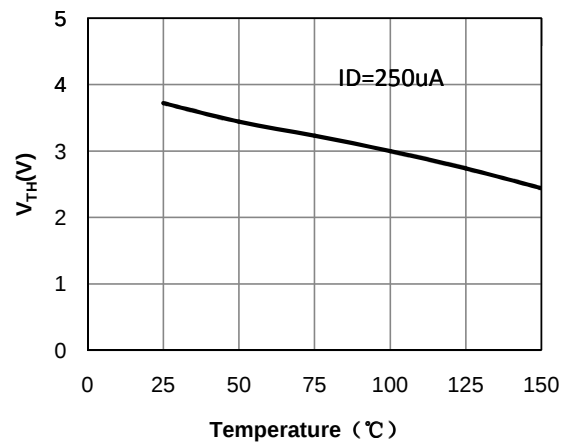


Fig 5: $R_{DS(on)}$ Vs I_{DS} Characteristics ($T_c=25^\circ\text{C}$)

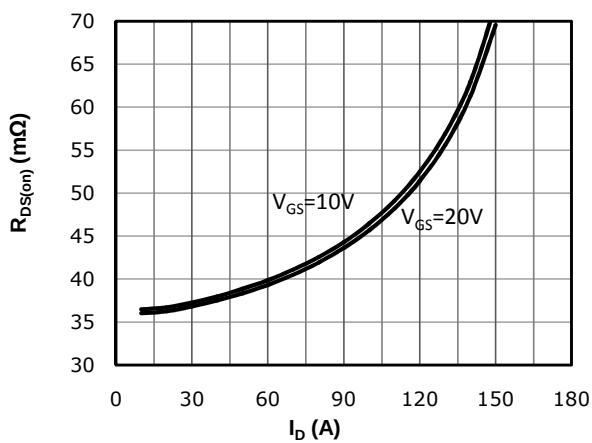


Fig 6: $R_{DS(on)}$ vs. Temperature

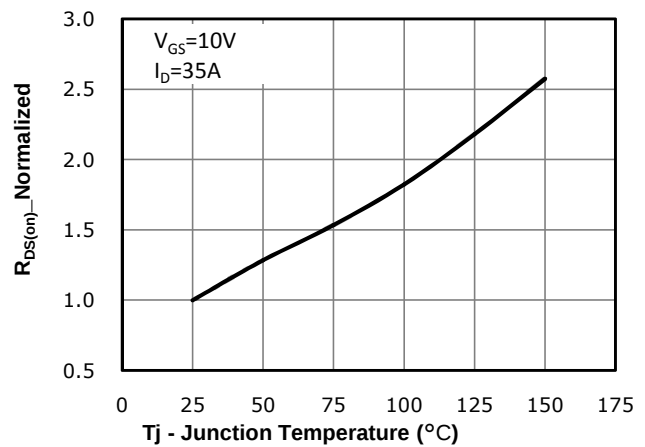


Fig 7: BVDSS vs. Temperature

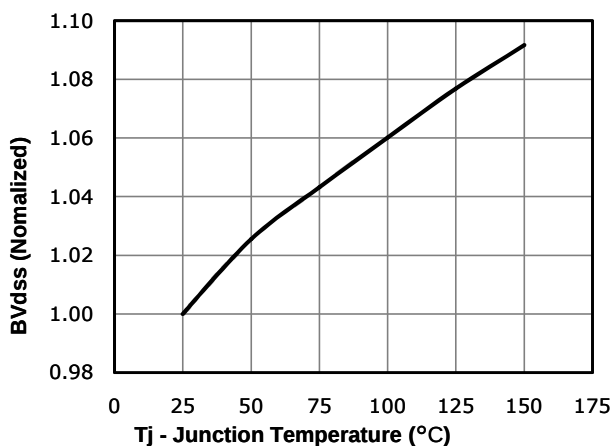


Fig 8: Rds(on) vs Gate Voltage

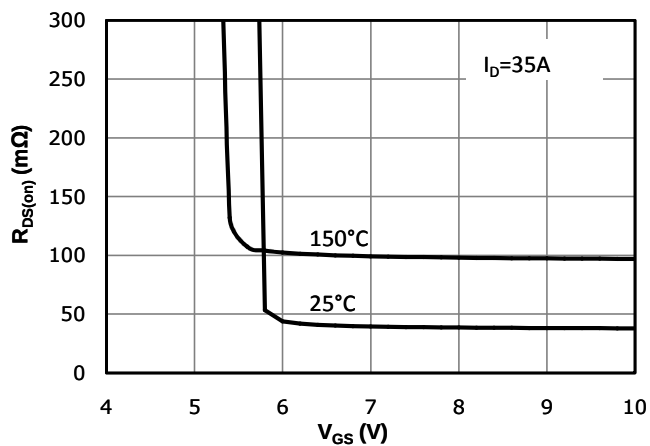


Fig 9: Body-diode Forward Characteristics

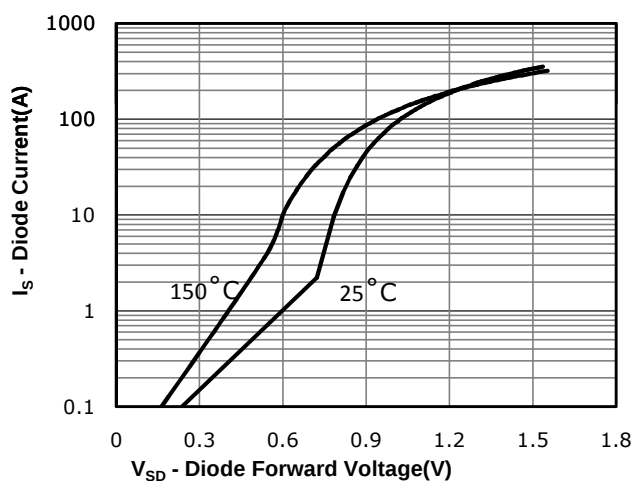


Fig 10: Gate Charge Characteristics

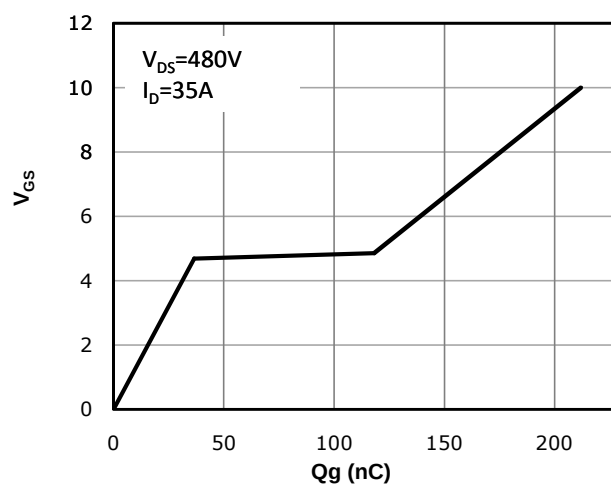


Fig 11: Capacitance Characteristics

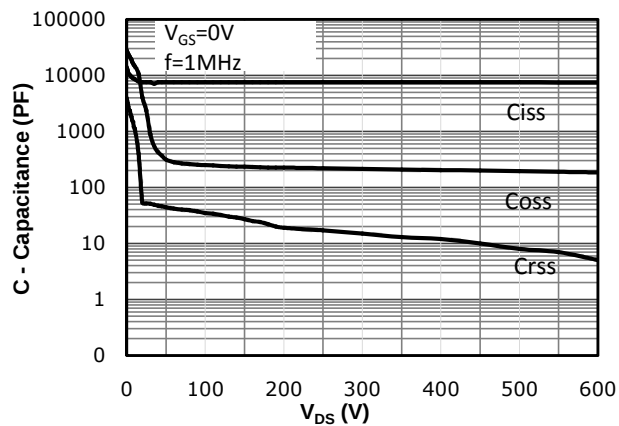


Fig 12: Safe Operating Area

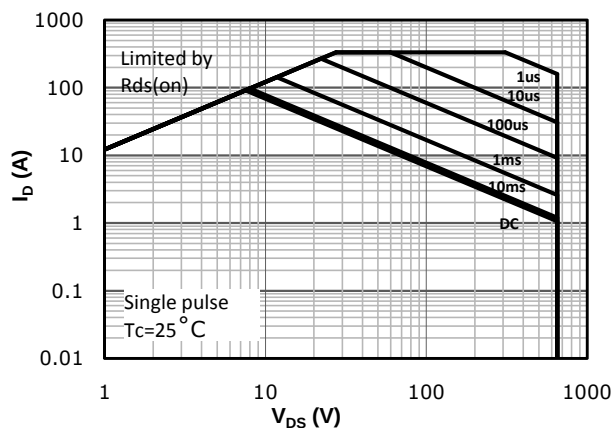
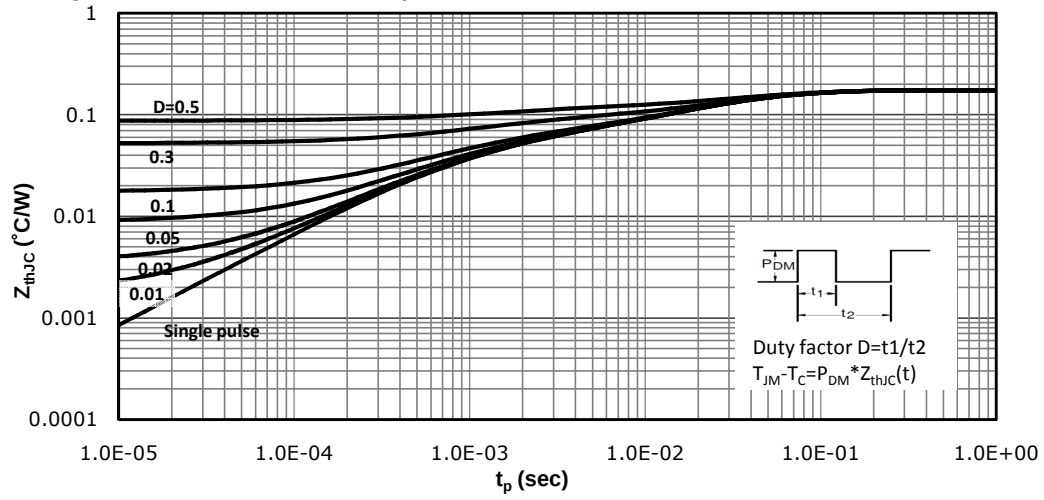
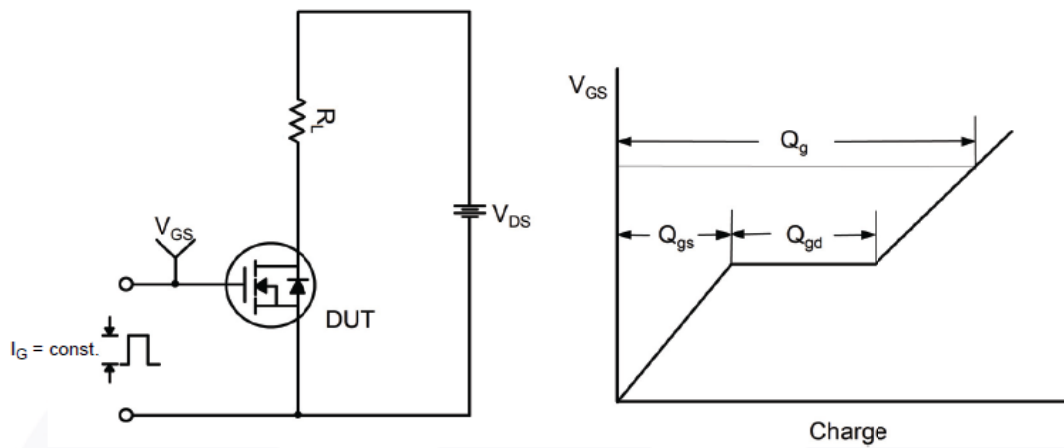


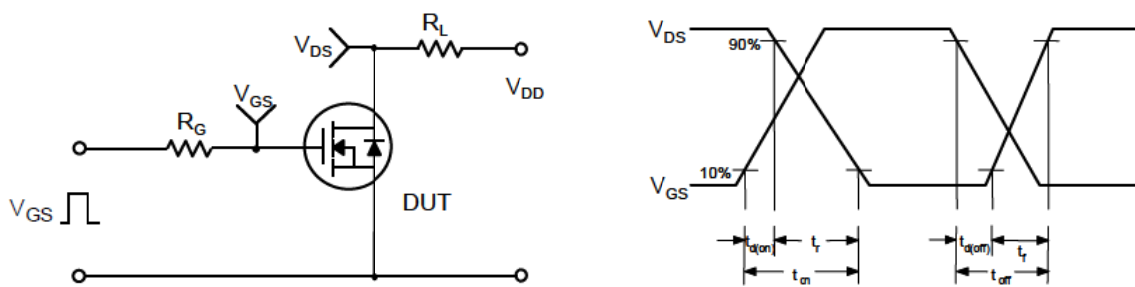
Fig 13: Max. Transient Thermal Impedance



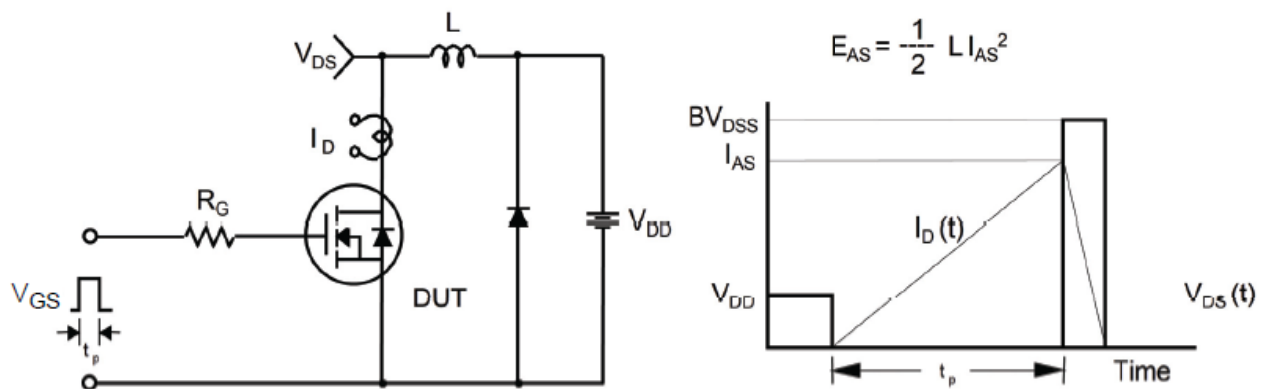
Gate Charge Test Circuit & Waveform



Switching Test Circuit & Waveforms

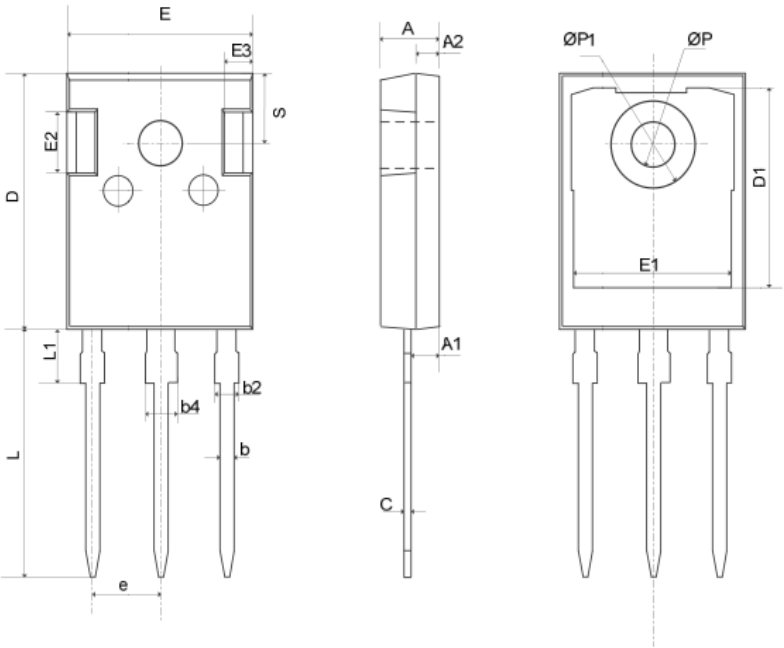


Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for TO-247

COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.11	1.36
b2	1.91	2.21
b4	2.91	3.21
c	0.51	0.75
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.00	13.60
E2	4.80	5.20
E3	2.30	2.70
e	5.44BSC	
L	19.62	20.22
L1	—	4.30
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	